

Wantae Lim

List of Publications by Year in descending order

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33
papers

1,557
citations

361413

20
h-index

414414

32
g-index

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all docs

33
docs citations

33
times ranked

1789
citing authors

#	ARTICLE	IF	CITATIONS
1	Light-Emitting Diodes with Hierarchical and Multifunctional Surface Structures for High Light Extraction and an Antifouling Effect. <i>Small</i> , 2016, 12, 161-168.	10.0	22
2	SiO ₂ nanohole arrays with high aspect ratio for InGaN/GaN nanorod-based phosphor-free white light-emitting-diodes. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2016, 34, 042204.	1.2	10
3	Light-Emitting Diodes: Light-Emitting Diodes with Hierarchical and Multifunctional Surface Structures for High Light Extraction and an Antifouling Effect (Small 2/2016). <i>Small</i> , 2016, 12, 138-138.	10.0	2
4	Titanium oxide nanotube arrays for high light extraction efficiency of GaN-based vertical light-emitting diodes. <i>Nanoscale</i> , 2016, 8, 10138-10144.	5.6	12
5	Enhanced optical output power of InGaN/GaN vertical light-emitting diodes by ZnO nanorods on plasma-treated N-face GaN. <i>Nanoscale</i> , 2014, 6, 10187-10192.	5.6	11
6	Light extraction efficiency of GaN-based LEDs with non-periodic and periodic sub-wavelength structures. <i>Journal of the Korean Physical Society</i> , 2013, 62, 770-774.	0.7	7
7	Effect of oxygen plasma treatment on nonalloyed Al/Ti-based contact for high power InGaN/GaN vertical light-emitting diodes. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2013, 31, 010602.	1.2	5
8	Metastable centers in AlGaIn/AlN/GaN heterostructures. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012, 30, .	1.2	14
9	Highly sensitive AlGaIn/GaN diode-based hydrogen sensors using platinum nanonetworks. <i>Sensors and Actuators B: Chemical</i> , 2012, 164, 64-68.	7.8	32
10	Hydrogen sensing characteristics of non-polar a-plane GaN Schottky diodes. <i>Current Applied Physics</i> , 2010, 10, 1029-1032.	2.4	20
11	Recent advances in wide bandgap semiconductor biological and gas sensors. <i>Progress in Materials Science</i> , 2010, 55, 1-59.	32.8	247
12	Effects of ambient atmosphere on the transfer characteristics and gate-bias stress stability of amorphous indium-gallium-zinc oxide thin-film transistors. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	121
13	Improvement in bias stability of amorphous-InGaZnO ₄ thin film transistors with SiO _x passivation layers. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2010, 28, 116-119.	1.2	32
14	Oxygen gas sensing at low temperature using indium zinc oxide-gated AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2010, 28, 376-379.	1.2	9
15	Temperature dependence of current-voltage characteristics of Ni ²⁺ /AlGaIn/GaN Schottky diodes. <i>Applied Physics Letters</i> , 2010, 97, .	3.3	49
16	Low-voltage indium gallium zinc oxide thin film transistors on paper substrates. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	74
17	Fabrication of compositional graded Si _{1-x} Gex layers by using thermal oxidation. <i>Applied Physics Letters</i> , 2009, 94, 202104.	3.3	6
18	High mobility InGaZnO ₄ thin-film transistors on paper. <i>Applied Physics Letters</i> , 2009, 94, .	3.3	87

#	ARTICLE	IF	CITATIONS
19	Recent Advances in Wide Bandgap Semiconductor Biological and Gas Sensors. Materials Research Society Symposia Proceedings, 2009, 1202, 138.	0.1	1
20	Growth and Characterization of GaN Nanowires for Hydrogen Sensors. Journal of Electronic Materials, 2009, 38, 490-494.	2.2	42
21	Hydrogen sensing with Pt-functionalized GaN nanowires. Sensors and Actuators B: Chemical, 2009, 140, 196-199.	7.8	82
22	Indium zinc oxide thin films deposited by sputtering at room temperature. Applied Surface Science, 2008, 254, 2878-2881.	6.1	32
23	Carrier concentration dependence of Ti ⁺ Au specific contact resistance on n-type amorphous indium zinc oxide thin films. Applied Physics Letters, 2008, 92, .	3.3	31
24	High-Performance Indium Gallium Zinc Oxide Transparent Thin-Film Transistors Fabricated by Radio-Frequency Sputtering. Journal of the Electrochemical Society, 2008, 155, H383.	2.9	94
25	RF Characteristics of Room-Temperature-Deposited, Small Gate Dimension Indium Zinc Oxide TFTs. Electrochemical and Solid-State Letters, 2008, 11, H60.	2.2	32
26	Stable room temperature deposited amorphous InGaZnO ₄ thin film transistors. Journal of Vacuum Science & Technology B, 2008, 26, 959.	1.3	66
27	High Temperature Stable Contacts for GaN HEMTs and LEDs. Materials Research Society Symposia Proceedings, 2008, 1108, 1.	0.1	0
28	Room temperature hydrogen detection using Pd-coated GaN nanowires. Applied Physics Letters, 2008, 93, .	3.3	91
29	High performance indium gallium zinc oxide thin film transistors fabricated on polyethylene terephthalate substrates. Applied Physics Letters, 2008, 93, .	3.3	107
30	Low-temperature-fabricated InGaZnO ₄ thin film transistors on polyimide clean-room tape. Applied Physics Letters, 2008, 93, .	3.3	41
31	Selective-hydrogen sensing at room temperature with Pt-coated InN nanobelts. Applied Physics Letters, 2008, 93, .	3.3	35
32	Room-Temperature-Deposited Indium-Zinc Oxide Thin Films with Controlled Conductivity. Electrochemical and Solid-State Letters, 2007, 10, H267.	2.2	11
33	Room temperature deposited indium zinc oxide thin film transistors. Applied Physics Letters, 2007, 90, 232103.	3.3	132